**Product data sheet** 

## 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection

## 3. Applications

- · Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor								
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V	
$V_{GS}$	gate-source voltage			-20	-	20	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	170	mA	
Static characteristics (per transistor)								
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 170 mA; $T_j$ = 25 °C		-	3	4.5	Ω	

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1		D1 D2
2	G1	gate TR1		
3	D2	drain TR2	0	$G1 \longrightarrow G2$
4	S2	source TR2	☐1 ☐2 ☐3	
5	G2	gate TR2	TSSOP6 (SOT363)	
6	D1	drain TR1		S1 S2 017aaa256

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
NX138AKS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

# 7. Marking

Table 4. Marking codes

Type number	Marking code
	[1]
NX138AKS	F8%

[1] % = placeholder for manufacturing site code

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor		_	'		
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	170	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	110	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	680	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	265	mW
			[1]	-	325	mW
		T <sub>sp</sub> = 25 °C		-	1.33	W
Per device				'		,
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	nin diode	,	1		-	
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	170	mA

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 60 V, dual N-channel Trench MOSFET

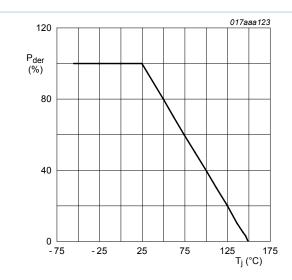


Fig. 1. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

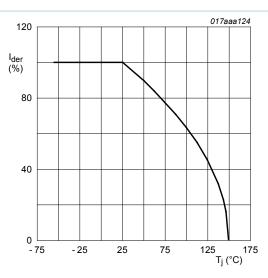
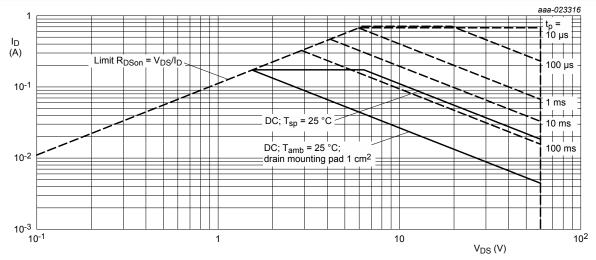


Fig. 2. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

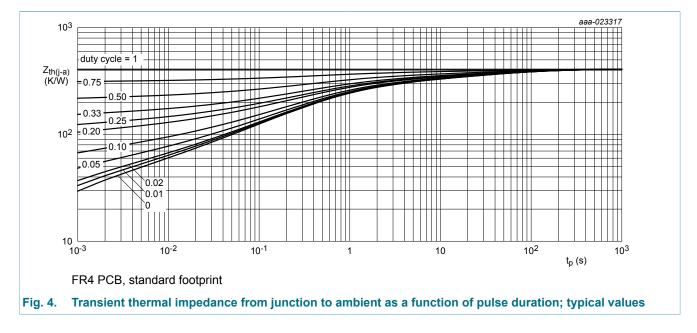
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### 9. Thermal characteristics

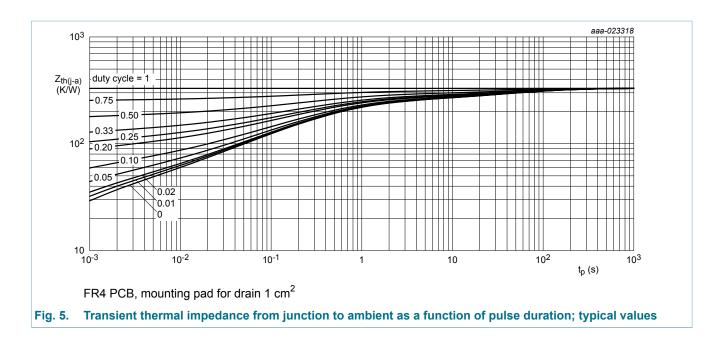
Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transist	Per transistor							
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1]	-	500	560	K/W	
		[2]	-	450	480	K/W		
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	100	115	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



### **60 V, dual N-channel Trench MOSFET**



**60 V, dual N-channel Trench MOSFET** 

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics (per transistor)					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \degree C$	0.8	1.1	1.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	2	μA
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-2	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.5	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.5	μΑ
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 25 °C	-	3	4.5	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 170 mA; T <sub>j</sub> = 150 °C	-	6	9	Ω
		$V_{GS}$ = 5 V; $I_D$ = 150 mA; $T_j$ = 25 °C	-	3.7	5.2	Ω
		$V_{GS}$ = 4 V; $I_D$ = 130 mA; $T_j$ = 25 °C	-	4	6.3	Ω
		V <sub>GS</sub> = 2.5 V; I <sub>D</sub> = 100 A; T <sub>j</sub> = 25 °C	-	5	10	Ω
9fs	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 170 mA; $T_{j}$ = 25 °C	-	3.5	-	S
Dynamic ch	naracteristics (per transist	or)	,			,
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = 30 V; $I_{D}$ = 170 mA; $V_{GS}$ = 10 V;	-	0.9	1.4	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.1	-	nC
$Q_{GD}$	gate-drain charge		-	0.2	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS} = 30 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	15	20	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	2.3	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	1.5	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 30 V; $I_{D}$ = 170 mA; $V_{GS}$ = 10 V;	-	8	12	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 75 \Omega; T_j = 25 °C$	-	10	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	8	20	ns
t <sub>f</sub>	fall time		-	5	-	ns
Source-dra	in diode (per transistor)				1	1
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 170 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.8	1.2	V

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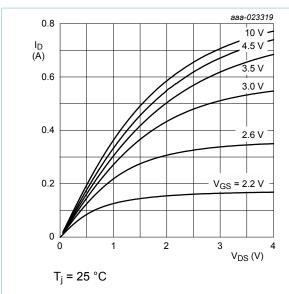


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

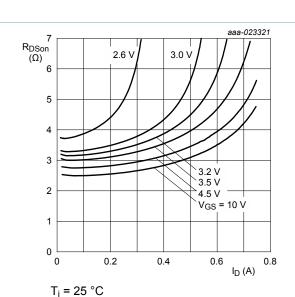


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

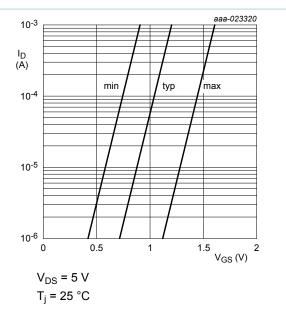


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

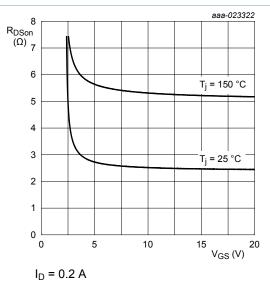


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

### 60 V, dual N-channel Trench MOSFET

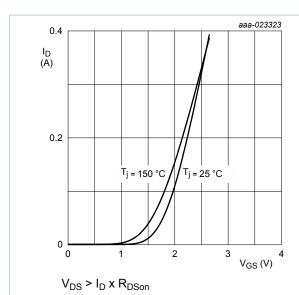


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

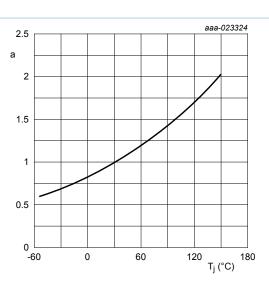


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

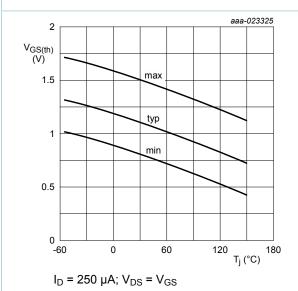


Fig. 12. Gate-source threshold voltage as a function of junction temperature

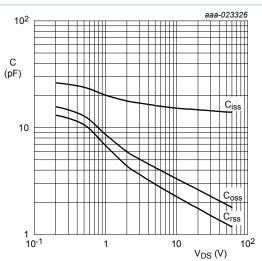


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

 $f = 1 MHz; V_{GS} = 0 V$ 

#### 60 V, dual N-channel Trench MOSFET

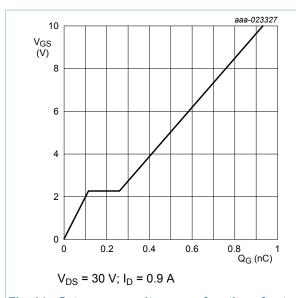


Fig. 14. Gate-source voltage as a function of gate charge; typical values

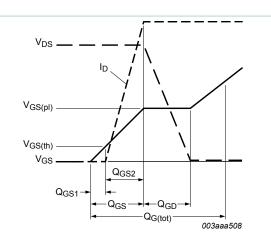


Fig. 15. MOSFET transistor: Gate charge waveform definitions

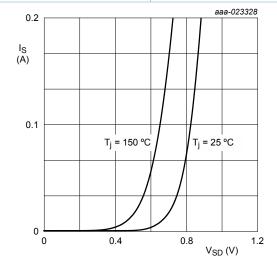
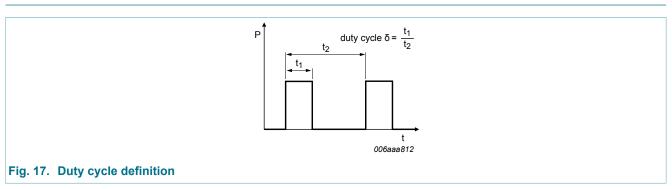


Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

 $V_{GS} = 0 V$ 

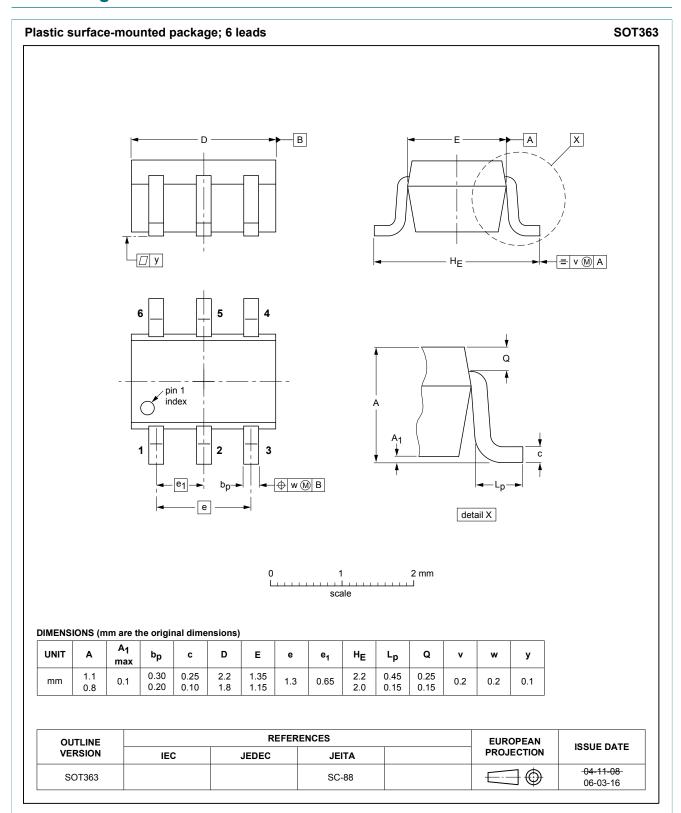


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# 12. Package outline

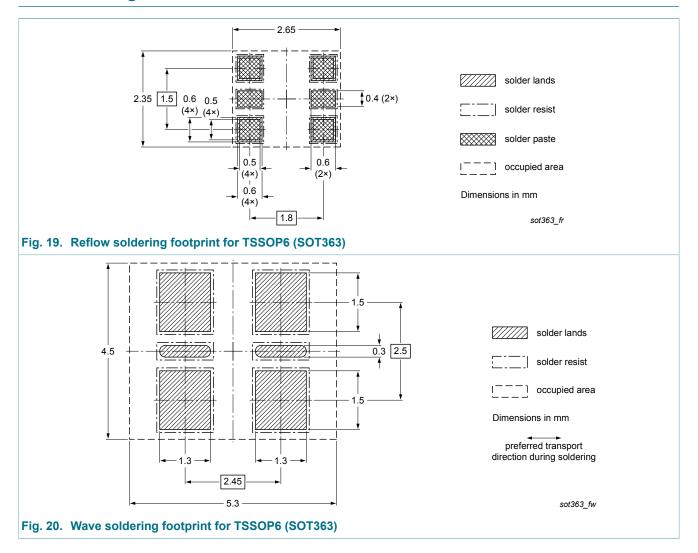


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### 60 V, dual N-channel Trench MOSFET

# 13. Soldering



**60 V, dual N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX138AKS v.1	20160615	Product data sheet	-	-

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#### 60 V, dual N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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